

LOW Voltage N-Channel MOSFET

◆ Features:

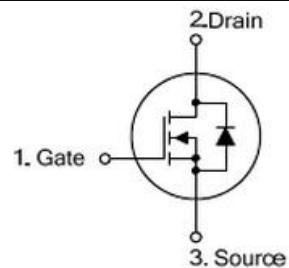
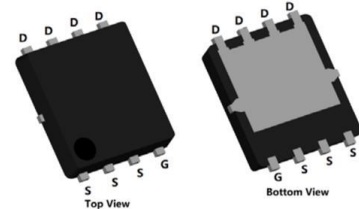
- ✧ Fast switching speed
开关速度快
- ✧ Low gate charge
低门充电
- ✧ High power and current handing capability
高功率和电流处理能力
- ✧ ROHS compliant
符合 ROHS 标准

◆ Applications

- ✧ DC to DC converters
直流到直流转换
- ✧ Synchronous Rectification
同步整流

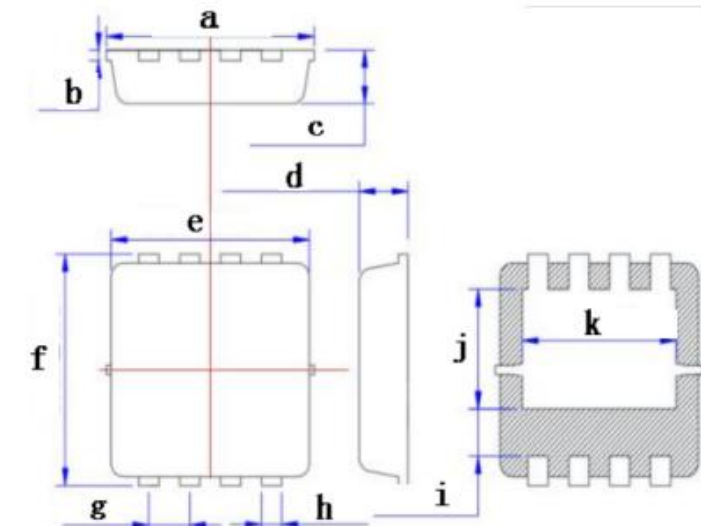


DFN5*6



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Unit:mm



DIM	MIN	MAX
a	5.10	5.30
b	0.20	0.50
c	0.90	1.10
d	0.85	1.05
e	5.10	5.30
f	6.00	6.20
g	1.05	1.25
h	0.25	0.45
i	1.10	1.30
j	3.40	3.60
k	3.90	4.10

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V _{DSS}	Drain-Source Voltage 漏源电压	100	V
V _{GS}	Gate-Source Voltage-Continuous 栅源电压	±20	V
I _D	Drain Current-Continuous (Note 2) 漏极持续电流	150	A
I _{DM}	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	600	A
P _D	Power Dissipation (Note 2) 功率损耗	195	W
T _j	Max.Operating junction temperature 最大结温	150	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B _V DSS	Drain-Source Breakdown Voltage Current (Note 1) 漏极击穿电压	100	--	--	V	I _D =250μA, V _{GS} =0V
V _{GS(th)}	Gate Threshold Voltage 栅极开启电压	1.0	--	3.0	V	V _{DS} =V _{GS} , I _D =250μA
R _{DS(on)}	Drain-Source On-Resistance 漏源导通电阻	--	6.0	7.0	mΩ	V _{GS} =10V, I _D =20A
I _{GSS}	Gate-Body Leakage Current 栅极漏电流	--	--	±100	nA	V _{GS} =±20V, V _{DS} =0
I _{DSS}	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	1	μA	V _{DS} =100V, V _{GS} =0
gfs	Forward Trans conductance 正向跨导	--	42	--	S	V _{DS} =5V, I _D =20A



OSN150N10G-OSEN

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Switching Characteristics						
T _{d (on)}	Turn-On Delay Time 开启延迟时间	--	20	--	ns	V _{DD} =50V, I _D =60A, R _G =4.7Ω
T _r	Rise Time 上升时间	--	80	--	ns	
T _{d (off)}	Turn-Off Delay Time 关闭延迟时间	--	50	--	ns	
T _f	Fall Time 下降时间	--	18	--	ns	
Q _g	Total Gate Charge 栅极总电荷	--	100	--	nC	V _{DS} =50V V _{GS} =10V, I _D =75A
Q _{gs}	Gate-Source Charge 栅源极电荷	--	45	--	nC	
Q _{gd}	Gate-Drain Charge 栅漏极电荷	--	20	--	nC	
Dynamic Characteristics						
C _{iss}	Input Capacitance 输入电容	--	3400	--	pF	V _{DS} =25V, V _{GS} =0, f=1MHz
C _{oss}	Output Capacitance 输出电容	--	550	--	pF	
C _{rss}	Reverse Transfer Capacitance 反向传输电容	--	75	--	pF	
I _S	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	150	A	
V _{SD}	Diode Forward On-Voltage 二极管正向导通电压	--	--	1.3	V	I _S =30A, V _{GS} =0
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	0.64	°C/W	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.